

FOR USE BY ELECTRICIANS OVERSEAS:

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_a=25^{\circ}\text{C}$)					電気的特性 ($T_a=25^{\circ}\text{C}$)											備考
				V_{ceo} (V)	V_{cso} (V)	I_c (mA)	P_c (mW)	T_j ($^{\circ}\text{C}$)	I_{cso} 最大値 (μA)	$V_{ce(V)}$	直流又はパルス h_{FE} I_c (mA)	バイアス $V_{ce(V)}$	h_{FE} h_{FE}^*	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)	$f_{\alpha b}$ $f_{\alpha b}^*$ (Mc)	C_{ob} (pF)	$r_{bb'}$ $h_{ie}(\text{real})^*$ (Ω)	
1	2	3	4	5					6	7		8			9				11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cso} MAXIMUM VALUE AND V_{ce} VALUE (CRITERIA FOR MEASURING I_{cso})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{ce} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{ce} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.

- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF $h_{ie}(\text{real})$
- 11 OUTLINE
- 12 REMARKS

: とコンプリ: COMPLEMENTARY TO

型 名	社 名	用 途	構 造	最大 定 格 (T _a = 25℃)					電 気 的 特 性 (T _a = 25℃)													外 形	備 考
				V _{CB0} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (℃)	I _{CB0} 最大値 (μA)	V _{CB} (V)	直 流 又 は バ ル ス hFE		β		h _{FE}		h _{FE} (Ω)	h _{FE} (×10 ⁻⁴)	h _{FE} (μU)	f _{ab} f _T * (Mc)	C _{ob} (pF)		
2SC2502	新電元	SW	Si.T	500	7	6 A	50W (T _a =25℃)	150	100	500	20	2	3 A	10	-600	t _{on} < 1 μS t _{off} < 3 μS	t _f < 0.7 μS		20 *			268	T6V40F1
" 2503	"	"	"	500	7	8 A	80W (T _a =25℃)	150	100	500	20	2	4 A	10	-1 A	t _{on} < 1 μS t _{off} < 3 μS	t _f < 0.7 μS		20 *			198	T8V40F1
" 2504	"	"	"	500	7	10A	100W (T _a =25℃)	150	100	500	20	2	5 A	10	-1 A	t _{on} < 1 μS t _{off} < 3 μS	t _f < 0.7 μS		20 *			198	T10V40F1
" 2505	"	"	"	500	7	3 A	60W (T _a =25℃)	150	100	500	20	2	1.5A	10	-300	t _{on} < 1 μS t _{off} < 3 μS	t _f < 0.7 μS		20 *			204	T3M40F1
" 2506	"	"	"	500	7	6 A	80W (T _a =25℃)	150	100	500	20	2	3 A	10	-600	t _{on} < 1 μS t _{off} < 3 μS	t _f < 0.7 μS		20 *			204	T6M40F1
" 2507	"	"	"	500	7	20A	200W (T _a =25℃)	150	100	500	20	2	10A	10	-2 A	t _{on} < 1 μS t _{off} < 3 μS	t _f < 0.7 μS		20 *			102	T20M40F1
" 2508	東 芝	PA	Si.EP	40	4	6 A	50W (T _a =25℃)	175	1mA	15	10~150	5	3 A			P _a > 27W, η > 60% (f=175MHz, V _{CC} =12.5V, P _i =4.2W)		<80			325		
" 2509	"	"	"	40	4	5 A	20W (T _a =25℃)	150			>20	5	1 A			P _a > 10W (PEP) (f=28MHz, V _{CC} =12.5V, P _i < 0.4W)		<150			268B		
" 2510	"	"	"	60	4	20A	250W (T _a =25℃)	175			>10	5	10A			P _a > 150W (PEP) (f=28MHz, V _{CC} =28V, P _i =7W)		450			281		
" 2511	日 立	RF. Mix	Si.E	60	4	100	320	125	0.2	25	41~175	3	1	6	-2	G _{ps} = 20dB (6 V, 1 mA, 100MHz)		150 *	2	C _{rss} = 10pS	138C		
" 2512	"	"	"	30	3	50	300	125	0.5	10	>30	10	10	10	-10	G _{ds} = 20dB (10V, 2 mA, 200MHz)		900 *	C _{re} 0.35	C _{rss} < 20pS	138C		
" 2513																							
" 2514																							
" 2515																							
" 2516	日 電	SW	Si.E	150	12	5 A	30W (T _a =25℃)	150	10	60	40~200	5	3 A			t _{on} < 0.5 μS t _{off} < 1.5 μS	t _f < 0.5 μS				268	2SA1069 とコンプリ	
" 2517	"	"	"	150	12	5 A	30W (T _a =25℃)	150	10	100	40~200	5	2 A			t _{on} < 0.5 μS t _{off} < 2 μS	t _f < 0.5 μS				268		
" 2518	"	"	Si.T	500	8	5 A	40W (T _a =25℃)	150	10	400	20~80	5	500			t _{on} < 1 μS t _{off} < 2.5 μS	t _f < 0.7 μS				268		
" 2519	松 下	RF	Si.EP	30	5	30	250	125	1	10	230	10	1	10	-1			230 *	0.8	20	38		
" 2520																							
" 2521																							
" 2522	富士通	PA	Si.P	120	5	12A	120W (T _a =25℃)	150	50	120	110	5	1 A	10	-1 A			80 *	180	1.5 *	102	2SA1072 とコンプリ	
" 2523	"	"	"	160	5	12A	120W (T _a =25℃)	150	50	160	110	5	1 A	10	-1 A			80 *	180	1.5 *	102	2SA1073 とコンプリ	
" 2524																							
" 2525	富士通	PA	Si.P	120	5	12A	120W (T _a =25℃)	150	50	120	110	5	1 A					80 *			163	2SA1075 とコンプリ	
" 2526	"	"	"	160	5	12A	120W (T _a =25℃)	150	50	160	110	5	1 A					80 *			163	2SA1076 とコンプリ	
" 2527	"	"	"	120	5	10A	60W (T _a =25℃)	150	50	120	110	5	1 A	10	-1 A			80 *	180	1.5 *	268	2SA1077 とコンプリ	
" 2528	"	"	"	120	5	2 A	25W (T _a =25℃)	150	1	120	120	5	300	10	-500			160 *	60	12 *	268	2SA1078 とコンプリ	
" 2529	"	"	"	160	5	2 A	25W (T _a =25℃)	150	1	160	120	5	300	10	-500			160 *	60	12 *	268	2SA1079 とコンプリ	
" 2530	"	"	"	40	7	500	20W (T _a =25℃)	150	0.1	40	150	5	10	10	-10			35 *	25	15 *	268		
" 2531																							